

Pb Free Plating Product

MUR1620G thru MUR1660G



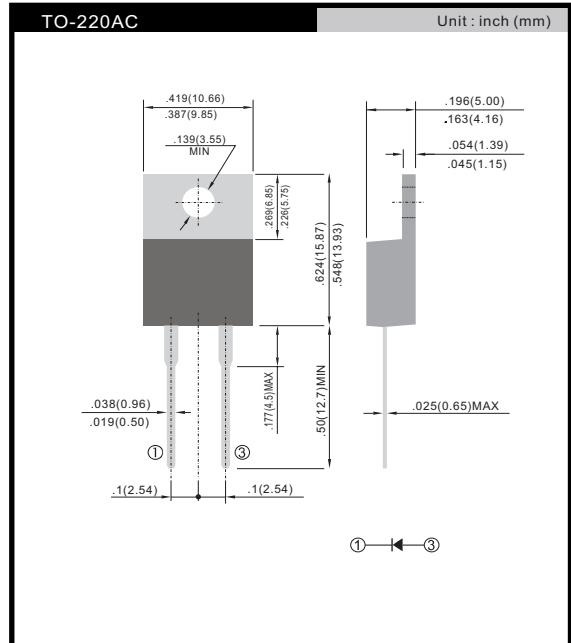
16.0 Ampere Heatsink Single Ultra Fast Recovery Rectifier Diodes

Features

- * Fast switching for high efficiency
- * Low forward voltage drop
- * High current capability
- * Low reverse leakage current
- * High surge current capability

Mechanical Data

- * Case: Molded TO-220AC
- * Epoxy: UL 94V-0 rate flame retardant
- * Terminals: Solderable per MIL-STD-202 method 208
- * Polarity: Color band denotes cathode
- * Mounting position: Any
- * Weight: 2.1 gram approximately



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating at 25°C ambient temperature unless otherwise specified.
 Single phase, half wave ,60Hz, resistive or inductive load.
 For capacitive load, derate current by 20%

CHARACTERISTICS	SYMBOL	MUR1620G	MUR1640G	MUR1660G	UNIT
Maximum Recurrent Peak Reverse Voltage	V _{RRM}	200	400	600	V
Maximum RMS Voltage	V _{RMS}	140	280	420	V
Maximum DC Blocking Voltage	V _{DC}	200	400	600	V
Maximum Average Forward Rectified Current @T _A =125°C	I _(AV)	16.0			A
Peak Forward Surge Current 8.3ms Single Half Sine-Wave Super Imposed on Rated Load(JEDEC Method)	I _{FSM}	300			A
Peak Forward Voltage at 16.0A DC	V _F	0.95	1.25	1.50	V
Maximum DC Reverse Current @T _J =25°C	I _R	5.0			μA
at Rated DC Blocking Voltage @T _J =125°C		50			
Maximum Reverse Recovery Time(Note1)	T _{RR}	35-50			nS
Typical Junction Capacitance (Note2)	C _J	80			pF
Typical Thermal Resistance (Note3)	R _{θJA}	2.0			°C/W
Operating and Storage Temperature Range	T _J ,T _{STG}	-55 to + 150			°C

NOTES:1.Measured with I_F=0.5A,I_R=1A,I_{RR}=0.25A
 2.Measured at 1.0 MHz and applied reverse voltage of 4.0VDC.
 3.Thermal resistance junction to ambient

RATING AND CHARACTERISTIC CURVES (MUR1620G thru MUR1660G)

